74LVC244A

Low-Voltage CMOS Octal Buffer

With 5 V−Tolerant Inputs and Outputs (3−State, Non−Inverting)

The 74LVC244A is a high performance, non−inverting octal buffer operating from a 1.2 to 3.6 V supply. High impedance TTL compatible inputs significantly reduce current loading to input drivers while TTL compatible outputs offer improved switching noise performance. A V_I specification of 5.5 V allows 74LVC244A inputs to be safely driven from 5 V devices. The 74LVC244A is suitable for memory address driving and all TTL level bus oriented transceiver applications.

Current drive capability is 24 mA at the outputs. The Output Enable ($\overline{OE}$) input, when HIGH, disables the output by placing them in a HIGH Z condition.

Features

- Designed for 1.2 V to 3.6 V V_{CC} Operation
- 5 V Tolerant − Interface Capability With 5 V TTL Logic
- Supports Live Insertion and Withdrawal
- I_{OFF} Specification Guarantees High Impedance When $V_{CC} = 0$ V
- 24 mA Output Sink and Source Capability
- Near Zero Static Supply Current in All Three Logic States (10 μA) Substantially Reduces System Power Requirements
- ESD Performance:
  - Human Body Model >2000 V
  - Machine Model >200 V
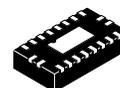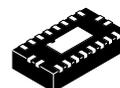- These Devices are Pb−Free, Halogen Free/BFR Free and are RoHS Compliant

ON Semiconductor®

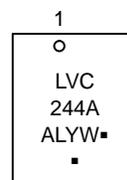| TSSOP−20 DT SUFFIX CASE 948E	QFN20 MN SUFFIX CASE 485AA	QFN20 MN SUFFIX CASE 485CB

MARKING DIAGRAMS

LVC
244A
ALYW▪

LVC
244A
ALYW▪

244A
ALYW▪
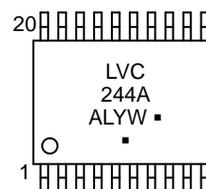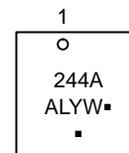
QFN20 − 485AA   QFN20 − 485CB

A	= Assembly Location
L	= Wafer Lot
Y	= Year
W	= Work Week
▪	= Pb−Free Package

(Note: Microdot may be in either location)

ORDERING INFORMATION

74LVC244A
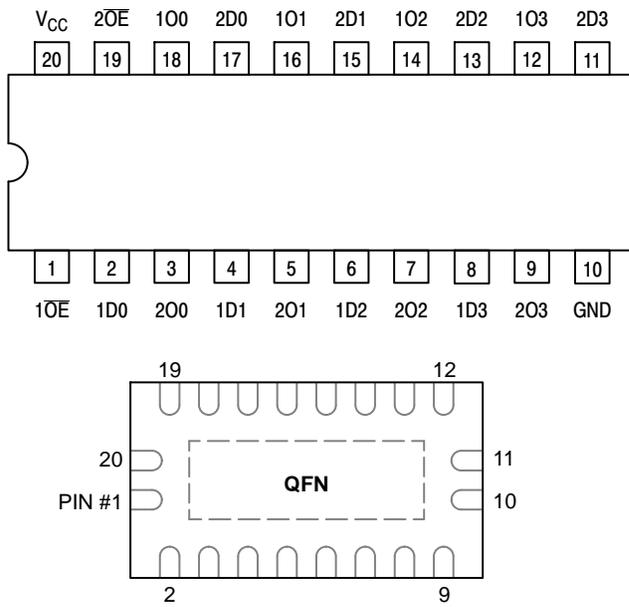
Figure 1. Pinout: 20–Lead (Top View)

Figure 2. Logic Diagram

PIN NAMES

PINS	FUNCTION
nOE	Output Enable Inputs
1Dn, 2Dn	Data Inputs
1On, 2On	3–State Outputs

TRUTH TABLE

INPUTS		OUTPUTS
1OE 2OE	1Dn 2Dn	1On, 2On
L	L	L
L	H	H
H	X	Z

H = High Voltage Level
L = Low Voltage Level
Z = High Impedance State
X = High or Low Voltage Level and Transitions are Acceptable
For I_{CC} reasons, DO NOT FLOAT Inputs

MAXIMUM RATINGS

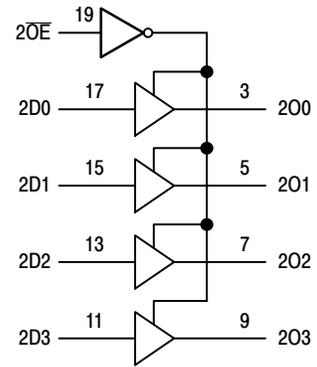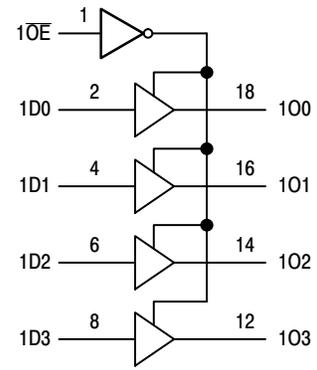| Symbol	Parameter	Condition	Value	Unit
V_{CC}	DC Supply Voltage		−0.5 to +6.5	V
V_I	DC Input Voltage		$−0.5 \leq V_I \leq +6.5$	V
V_O	DC Output Voltage	Output in 3−State	$−0.5 \leq V_O \leq +6.5$	V
		Output in HIGH or LOW State (Note 1)	$−0.5 \leq V_O \leq V_{CC} + 0.5$	V
I_{IK}	DC Input Diode Current	$V_I < GND$	−50	mA
I_{OK}	DC Output Diode Current	$V_O < GND$	−50	mA
		$V_O > V_{CC}$	+50	mA
I_O	DC Output Source/Sink Current		±50	mA
I_{CC}	DC Supply Current Per Supply Pin		±100	mA
I_{GND}	DC Ground Current Per Ground Pin		±100	mA
T_{STG}	Storage Temperature Range		−65 to +150	°C
T_L	Lead Temperature, 1 mm from Case for 10 Seconds		$T_L = 260$	°C
T_J	Junction Temperature Under Bias		$T_J = 135$	°C
θ_{JA}	Thermal Resistance (Note 2)		110.7	°C/W
MSL	Moisture Sensitivity	Level 1		

Stresses exceeding those listed in the Maximum Ratings table may damage the device. If any of these limits are exceeded, device functionality should not be assumed, damage may occur and reliability may be affected.
1. I_O absolute maximum rating must be observed.
2. Measured with minimum pad spacing on an FR4 board, using 10 mm−by−1 inch, 2 ounce copper trace no air flow.

RECOMMENDED OPERATING CONDITIONS

Symbol	Parameter	Min	Typ	Max	Units
V_{CC}	Supply Voltage Operating Functional	1.65 1.2		3.6 3.6	V
V_I	Input Voltage	0		5.5	V
V_O	Output Voltage HIGH or LOW State 3−State	0 0		V_{CC} 5.5	V
I_{OH}	HIGH Level Output Current $V_{CC} = 3.0 V – 3.6 V$ $V_{CC} = 2.7 V – 3.0 V$			−24 −12	mA
I_{OL}	LOW Level Output Current $V_{CC} = 3.0 V – 3.6 V$ $V_{CC} = 2.7 V – 3.0 V$			24 12	mA
T_A	Operating Free−Air Temperature	−40		+125	°C
$\Delta t/\Delta V$	Input Transition Rise or Fall Rate $V_{CC} = 1.65 V$ to $2.7 V$ $V_{CC} = 2.7 V$ to $3.6 V$	0 0		20 10	ns/V

Functional operation above the stresses listed in the Recommended Operating Ranges is not implied. Extended exposure to stresses beyond the Recommended Operating Ranges limits may affect device reliability.

DC ELECTRICAL CHARACTERISTICS

Symbol	Parameter	Conditions	−40°C to +85°C			−40°C to +125°C			Unit
			Min	Typ (Note 3)	Max	Min	Typ (Note 3)	Max	
V_{IH}	HIGH−level input voltage	V_{CC} = 1.2 V	1.08	–	–	1.08	–	–	V
		V_{CC} = 1.65 V to 1.95 V	0.65 x V_{CC}	–	–	0.65 x V_{CC}	–	–	
		V_{CC} = 2.3 V to 2.7 V	1.7	–	–	1.7	–	–	
		V_{CC} = 2.7 V to 3.6 V	2.0	–	–	2.0	–	–	
V_{IL}	LOW−level input voltage	V_{CC} = 1.2 V	–	–	0.12	–	–	0.12	V
		V_{CC} = 1.65 V to 1.95 V	–	–	0.35 x V_{CC}	–	–	0.35 x V_{CC}	
		V_{CC} = 2.3 V to 2.7 V	–	–	0.7	–	–	0.7	
		V_{CC} = 2.7 V to 3.6 V	–	–	0.8	–	–	0.8	
V_{OH}	HIGH−level output voltage	V_I = V_{IH} or V_{IL}							V
		I_O = −100 μA; V_{CC} = 1.65 V to 3.6 V	V_{CC} − 0.2	–	–	V_{CC} − 0.3	–	–	
		I_O = −4 mA; V_{CC} = 1.65 V	1.2	–	–	1.05	–	–	
		I_O = −8 mA; V_{CC} = 2.3 V	1.8	–	–	1.65	–	–	
		I_O = −12 mA; V_{CC} = 2.7 V	2.2	–	–	2.05	–	–	
		I_O = −18 mA; V_{CC} = 3.0 V	2.4	–	–	2.25	–	–	
		I_O = −24 mA; V_{CC} = 3.0 V	2.2	–	–	2.0	–	–	
VOL	LOW−level output voltage	V_I = V_{IH} or V_{IL}							V
		I_O = 100 μA; V_{CC} = 1.65 V to 3.6 V	–	–	0.2	–	–	0.3	
		I_O = 4 mA; V_{CC} = 1.65 V	–	–	0.45	–	–	0.65	
		I_O = 8 mA; V_{CC} = 2.3 V	–	–	0.6	–	–	0.8	
		I_O = 12 mA; V_{CC} = 2.7 V	–	–	0.4	–	–	0.6	
		I_O = 24 mA; V_{CC} = 3.0 V	–	–	0.55	–	–	0.8	
I_I	Input leakage current	V_I = 5.5V or GND V_{CC} = 3.6 V	–	±0.1	±5	–	±0.1	±20	μA
I_{OZ}	OFF−state output current	VI = VIH or VIL; V_O = 5.5 V or GND; V_{CC} = 3.6 V	–	±0.1	±5	–	±0.1	±20	μA
I_{OFF}	Power−off leakage current	V_I or V_O = 5.5 V; V_{CC} = 0.0 V	–	±0.1	±10	–	±0.1	±20	μA
I_{CC}	Supply current	V_I = V_{CC} or GND; I_O = 0 A; V_{CC} = 3.6 V	–	0.1	10	–	0.1	40	μA
ΔI_{CC}	Additional supply current	per input pin; V_I = V_{CC} − 0.6 V; I_O = 0 A; V_{CC} = 2.7 V to 3.6 V	–	5	500	–	5	5000	μA

Product parametric performance is indicated in the Electrical Characteristics for the listed test conditions, unless otherwise noted. Product performance may not be indicated by the Electrical Characteristics if operated under different conditions.
3. All typical values are measured at T_A = 25°C and V_{CC} = 3.3 V, unless stated otherwise.

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AC ELECTRICAL CHARACTERISTICS ($t_R = t_F = 2.5$ ns)

Symbol	Parameter	Conditions	−40°C to +85°C			−40°C to +125°C			Unit
			Min	Typ[1]	Max	Min	Typ[1]	Max	
t_{pd}	Propagation Delay (Note 5) nDn to nOn	V_{CC} = 1.2 V	–	17.0	–	–	–	–	ns
		V_{CC} = 1.65 V to 1.95 V	1.5	6.4	13.7	1.5	–	15.8	
		V_{CC} = 2.3 V to 2.7 V	1.0	3.4	7.1	1.0	–	8.2	
		V_{CC} = 2.7 V	1.5	3.4	6.9	1.5	–	9.0	
		V_{CC} = 3.0 V to 3.6 V	1.5	2.9	5.9	1.5	–	7.5	
t_{en}	Enable Time (Note 6) nOE to nOn	V_{CC} = 1.2 V	–	24.0	–	–	–	–	ns
		V_{CC} = 1.65 V to 1.95 V	1.5	7.0	17.3	1.5	–	20.0	
		V_{CC} = 2.3 V to 2.7 V	1.5	3.9	9.5	1.5	–	11.0	
		V_{CC} = 2.7 V	1.5	4.1	8.6	1.5	–	11.0	
		V_{CC} = 3.0 V to 3.6 V	1.0	3.2	7.6	1.0	–	9.5	
t_{dis}	Disable Time (Note 7) nOE to nOn	V_{CC} = 1.2 V	–	9.0	–	–	–	–	ns
		V_{CC} = 1.65 V to 1.95 V	2.2	4.5	9.8	2.2	–	11.3	
		V_{CC} = 2.3 V to 2.7 V	0.5	3.6	5.5	0.5	–	6.4	
		V_{CC} = 2.7 V	1.5	3.3	6.8	1.5	–	8.5	
		V_{CC} = 3.0 V to 3.6 V	1.5	3.1	5.8	1.5	–	7.5	
$t_{sk(0)}$	Output Skew Time (Note 8)		–	–	1	–	–	1.5	ns

Product parametric performance is indicated in the Electrical Characteristics for the listed test conditions, unless otherwise noted. Product performance may not be indicated by the Electrical Characteristics if operated under different conditions.
4. Typical values are measured at T_A = 25°C and V_{CC} = 3.3 V, unless stated otherwise.
5. t_{pd} is the same as t_{PLH} and t_{PHL}.
6. t_{en} is the same as t_{PZL} and t_{PZH}.
7. t_{dis} is the same as t_{PLZ} and t_{PHZ}.
8. Skew between any two outputs of the same package switching in the same direction. This parameter is guaranteed by design.

DYNAMIC SWITCHING CHARACTERISTICS

Symbol	Characteristic	Condition	T_A = +25°C			Unit
			Min	Typ	Max	
V_{OLP}	Dynamic LOW Peak Voltage (Note 9)	V_{CC} = 3.3 V, C_L = 50 pF, V_{IH} = 3.3 V, V_{IL} = 0 V V_{CC} = 2.5 V, C_L = 30 pF, V_{IH} = 2.5 V, V_{IL} = 0 V		0.8 0.6		V
V_{OLV}	Dynamic LOW Valley Voltage (Note 9)	V_{CC} = 3.3 V, C_L = 50 pF, V_{IH} = 3.3 V, V_{IL} = 0 V V_{CC} = 2.5 V, C_L = 30 pF, V_{IH} = 2.5 V, V_{IL} = 0 V		−0.8 −0.6		V

9. Number of outputs defined as "n". Measured with "n−1" outputs switching from HIGH−to−LOW or LOW−to−HIGH. The remaining output is measured in the LOW state.

CAPACITIVE CHARACTERISTICS

Symbol	Parameter	Condition	Typical	Unit
C_{IN}	Input Capacitance	V_{CC} = 3.3 V, V_I = 0 V or V_{CC}	4	pF
C_{OUT}	Output Capacitance	V_{CC} = 3.3 V, V_I = 0 V or V_{CC}	5	pF
C_{PD}	Power Dissipation Capacitance (Note 10)	Per input; V_I = GND or V_{CC}		pF
		V_{CC} = 1.65 V to 1.95 V	6.4	
		V_{CC} = 2.3 V to 2.7 V	9.6	
		V_{CC} = 3.0 V to 3.6 V	12.5	

10. C_{PD} is used to determine the dynamic power dissipation (P_D in μW).
$P_D = C_{PD} \times V_{CC}^2 \times f_i \times N + \Sigma (C_L \times V_{CC}^2 \times f_o)$ where:
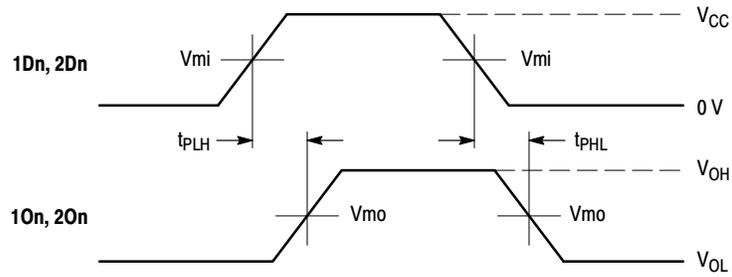f_i = input frequency in MHz; f_o = output frequency in MHz
C_L = output load capacitance in pF V_{CC} = supply voltage in Volts
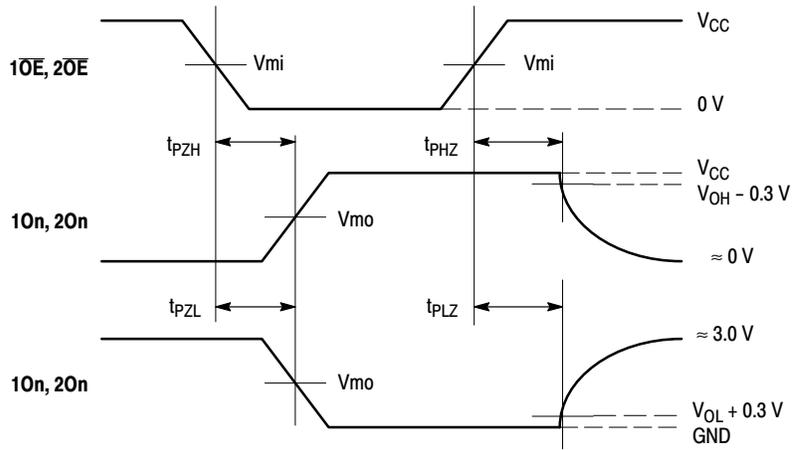N = number of outputs switching
$\Sigma(C_L \times V_{CC}^2 \times f_o)$ = sum of the outputs.

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WAVEFORM 1 – PROPAGATION DELAYS
$t_R = t_F$ = 2.5 ns, 10% to 90%; f = 1 MHz; t_W = 500 ns

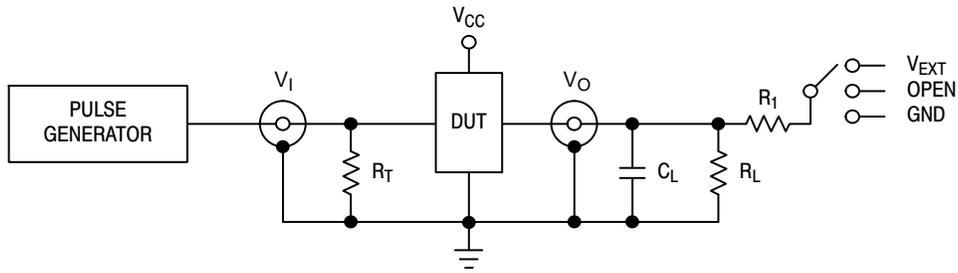**WAVEFORM 2 – OUTPUT ENABLE AND DISABLE TIMES**
$t_R = t_F$ = 2.5 ns, 10% to 90%; f = 1 MHz; t_W = 500 ns

Figure 3. AC Waveforms

Symbol	V_{CC}		
	3.3 V $\pm$ 0.3 V	**2.7 V**	**V_{CC} < 2.7 V**
Vmi	1.5 V	1.5 V	$V_{CC}/2$
Vmo	1.5 V	1.5 V	$V_{CC}/2$
V_{HZ}	V_{OL} + 0.3 V	V_{OL} + 0.3 V	V_{OL} + 0.15 V
V_{LZ}	V_{OH} – 0.3 V	V_{OH} – 0.3 V	V_{OH} – 015 V

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C_L includes jig and probe capacitance
R_T = Z_{OUT} of pulse generator (typically 50 Ω)
R_1 = R_L

Supply Voltage	Input		Load		V_{EXT}		
V_{CC} (V)	V_I	t_r, t_f	C_L	R_L	t_{PLH}, t_{PHL}	t_{PLZ}, t_{PZL}	t_{PHZ}, t_{PZH}
1.2	V_{CC}	≤ 2 ns	30 pF	1 kΩ	Open	2 x V_{CC}	GND
1.65 – 1.95	V_{CC}	≤ 2 ns	30 pF	1 kΩ	Open	2 x V_{CC}	GND
2.3 – 2.7	V_{CC}	≤ 2 ns	30 pF	500 Ω	Open	2 x V_{CC}	GND
2.7	2.7 V	≤ 2.5 ns	50 pF	500 Ω	Open	2 x V_{CC}	GND
3 – 3.6	2.7 V	≤ 2.5 ns	50 pF	500 Ω	Open	2 x V_{CC}	GND

Figure 4. Test Circuit

ORDERING INFORMATION

Device	Package	Shipping†
74LVC244ADTR2G	TSSOP–20 (Pb–Free)	2500 / Tape & Reel
74LVC244AMN2TWG (In Development)	QFN20, 2.5x3.5 (Pb–Free)	3000 / Tape & Reel
74LVC244AMNTWG (In Development)	QFN20, 2.5x4.5 (Pb–Free)	3000 / Tape & Reel

†For information on tape and reel specifications, including part orientation and tape sizes, please refer to our Tape and Reel Packaging Specifications Brochure, BRD8011/D.

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PACKAGE DIMENSIONS

TSSOP−20
CASE 948E−02
ISSUE C
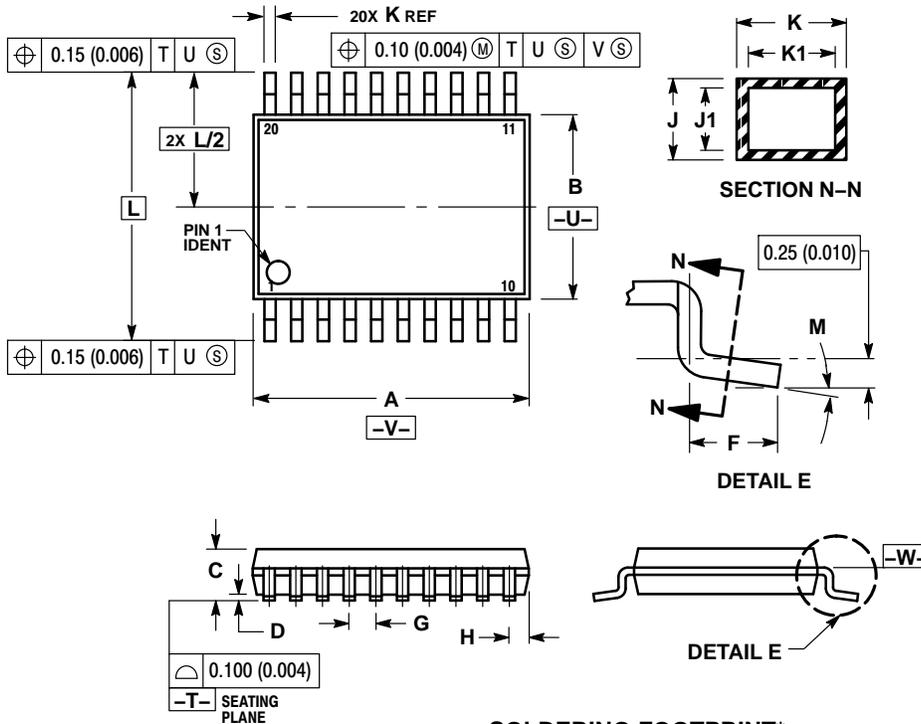
NOTES:
1. DIMENSIONING AND TOLERANCING PER ANSI Y14.5M, 1982.
2. CONTROLLING DIMENSION: MILLIMETER.
3. DIMENSION A DOES NOT INCLUDE MOLD FLASH, PROTRUSIONS OR GATE BURRS. MOLD FLASH OR GATE BURRS SHALL NOT EXCEED 0.15 (0.006) PER SIDE.
4. DIMENSION B DOES NOT INCLUDE INTERLEAD FLASH OR PROTRUSION. INTERLEAD FLASH OR PROTRUSION SHALL NOT EXCEED 0.25 (0.010) PER SIDE.
5. DIMENSION K DOES NOT INCLUDE DAMBAR PROTRUSION. ALLOWABLE DAMBAR PROTRUSION SHALL BE 0.08 (0.003) TOTAL IN EXCESS OF THE K DIMENSION AT MAXIMUM MATERIAL CONDITION.
6. TERMINAL NUMBERS ARE SHOWN FOR REFERENCE ONLY.
7. DIMENSION A AND B ARE TO BE DETERMINED AT DATUM PLANE −W−.

DIM	MILLIMETERS		INCHES	
	MIN	MAX	MIN	MAX
A	6.40	6.60	0.252	0.260
B	4.30	4.50	0.169	0.177
C	---	1.20	---	0.047
D	0.05	0.15	0.002	0.006
F	0.50	0.75	0.020	0.030
G	0.65 BSC		0.026 BSC	
H	0.27	0.37	0.011	0.015
J	0.09	0.20	0.004	0.008
J1	0.09	0.16	0.004	0.006
K	0.19	0.30	0.007	0.012
K1	0.19	0.25	0.007	0.010
L	6.40 BSC		0.252 BSC	
M	0°	8°	0°	8°

SOLDERING FOOTPRINT*
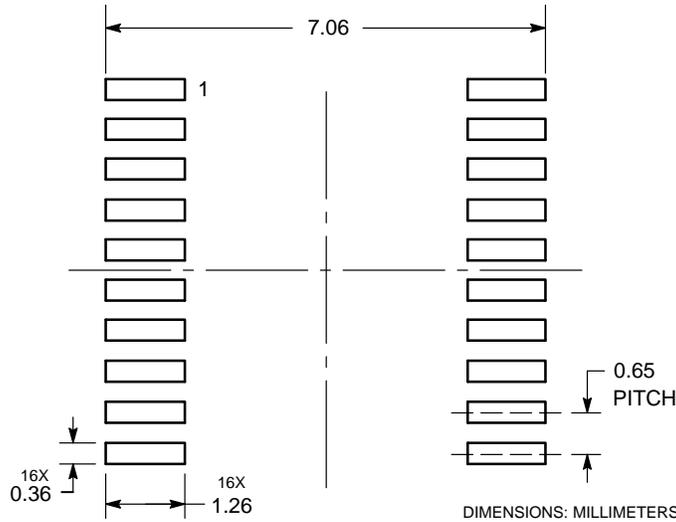
DIMENSIONS: MILLIMETERS

*For additional information on our Pb−Free strategy and soldering details, please download the ON Semiconductor Soldering and Mounting Techniques Reference Manual, SOLDERRM/D.

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PACKAGE DIMENSIONS

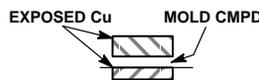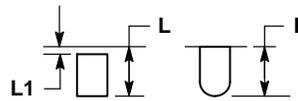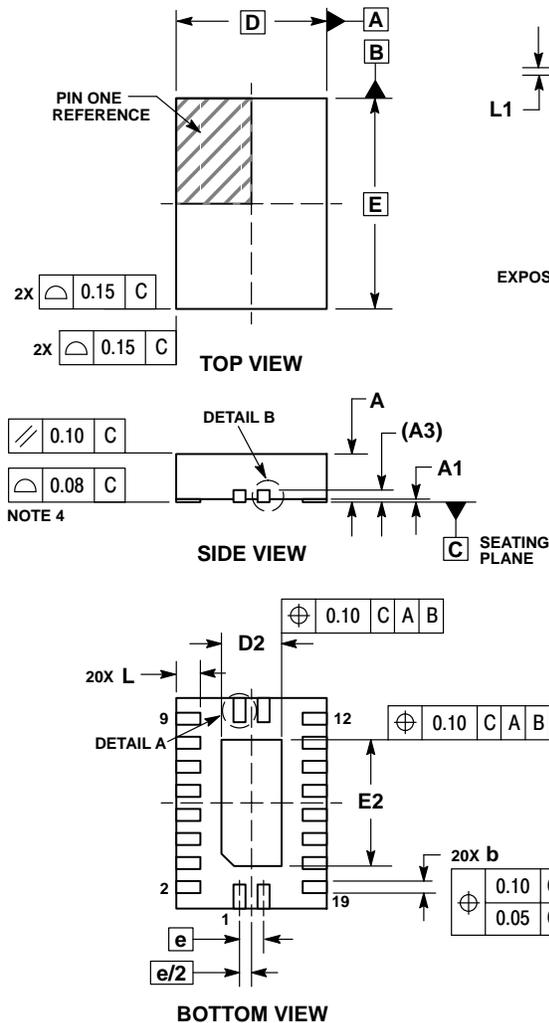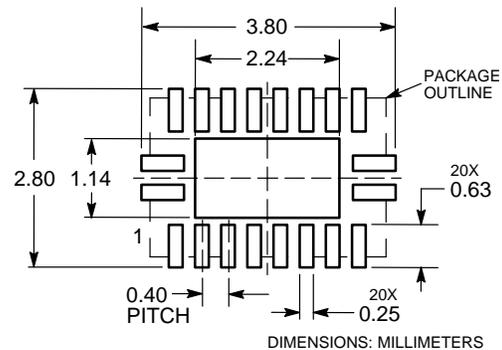**QFN20, 2.5x4.5 MM**
CASE 485AA
ISSUE B
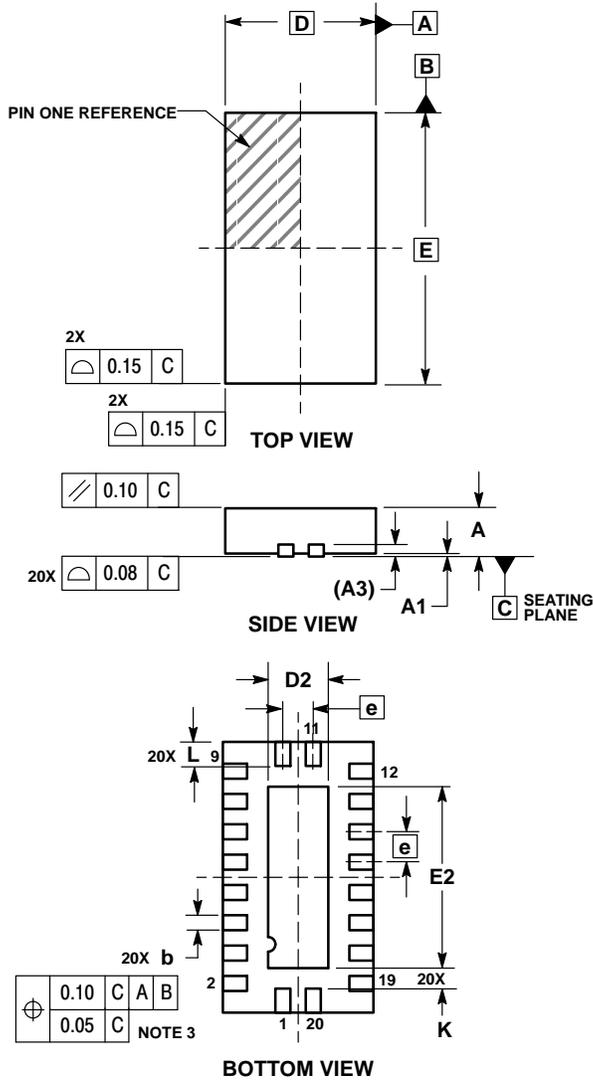
NOTES:
1. DIMENSIONING AND TOLERANCING PER ASME Y14.5M, 1994.
2. CONTROLLING DIMENSION: MILLIMETERS.
3. DIMENSIONS b APPLIES TO PLATED TERMINAL AND IS MEASURED BETWEEN 0.25 AND 0.30 MM FROM TERMINAL.
4. COPLANARITY APPLIES TO THE EXPOSED PAD AS WELL AS THE TERMINALS.

DIM	MILLIMETERS	
	MIN	MAX
A	0.80	1.00
A1	0.00	0.05
A3	0.20 REF	
b	0.20	0.30
D	2.50 BSC	
D2	0.85	1.15
E	4.50 BSC	
E2	2.85	3.15
e	0.50 BSC	
K	0.20	---
L	0.35	0.45

PIN ONE REFERENCE

2X [△ 0.15 | C]
2X [△ 0.15 | C]

TOP VIEW

[∥ 0.10 | C]
20X [△ 0.08 | C]

(A3)
A1
A
[C] SEATING PLANE

SIDE VIEW

20X L 9
11
[e]
12
[e]
E2
20X b
2
1 20
19 20X
K
[⊕ 0.10 | C | A | B]
[0.05 | C] NOTE 3

BOTTOM VIEW

74LVC244A

PACKAGE DIMENSIONS

QFN20, 2.5x3.5, 0.4P
CASE 485CB
ISSUE O

NOTES:
1. DIMENSIONING AND TOLERANCING PER ASME Y14.5M, 1994.
2. CONTROLLING DIMENSION: MILLIMETERS.
3. DIMENSIONS b APPLIES TO PLATED TERMINAL AND IS MEASURED BETWEEN 0.15 AND 0.30 MM FROM TERMINAL TIP.
4. COPLANARITY APPLIES TO THE EXPOSED PAD AS WELL AS THE TERMINALS.

DIM	MILLIMETERS	
	MIN	MAX
A	0.80	1.00
A1	0.00	0.05
A3	0.20 REF	
b	0.15	0.25
D	2.50 BSC	
D2	0.90	1.10
E	3.50 BSC	
E2	2.00	2.20
e	0.40 BSC	
L	0.35	0.45
L1	---	0.15

PIN ONE REFERENCE

2X [⌒] 0.15 C

2X [⌒] 0.15 C

TOP VIEW

L

L

L1

DETAIL A
ALTERNATE TERMINAL CONSTRUCTIONS

EXPOSED Cu   MOLD CMPD

DETAIL B
ALTERNATE CONSTRUCTIONS

[⫽] 0.10 C

[⌒] 0.08 C

NOTE 4

SIDE VIEW

A
(A3)
A1

[▽] C SEATING PLANE

DETAIL B

BOTTOM VIEW

[⊕] 0.10 C A B

D2

20X L

DETAIL A

9

12

[⊕] 0.10 C A B

E2

20X b

[⊕] 0.10 C A B
[⊕] 0.05 C   NOTE 3

2

1

19

e

e/2

BOTTOM VIEW

SOLDERING FOOTPRINT*

3.80

2.24

PACKAGE OUTLINE

2.80   1.14

20X 0.63

1

20X 0.25

0.40 PITCH

20X 0.25

DIMENSIONS: MILLIMETERS

*For additional information on our Pb–Free strategy and soldering details, please download the ON Semiconductor Soldering and Mounting Techniques Reference Manual, SOLDERRM/D.

74LVC244A/D

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ВМЕСТЕ МЫ СОЗДАЕМ БУДУЩЕЕ

ПОСТАВКА
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Данный компонент на территории Российской Федерации

Вы можете приобрести в компании MosChip.

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В нашем ассортименте представлены ведущие мировые производители активных и пассивных электронных компонентов.

Нашей специализацией является поставка электронной компонентной базы двойного назначения, продукции таких производителей как XILINX, Intel (ex.ALTERA), Vicor, Microchip, Texas Instruments, Analog Devices, Mini-Circuits, Amphenol, Glenair.

Сотрудничество с глобальными дистрибьюторами электронных компонентов, предоставляет возможность заказывать и получать с международных складов практически любой перечень компонентов в оптимальные для Вас сроки.

На всех этапах разработки и производства наши партнеры могут получить квалифицированную поддержку опытных инженеров.

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